Silicon PNP Power Transistors 2SA770 2SA771

DESCRIPTION

- With TO-220 package
- Complement to type 2SC1985/1986
- Low collector saturation voltage

APPLICATIONS

- For general and industrial purpose applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

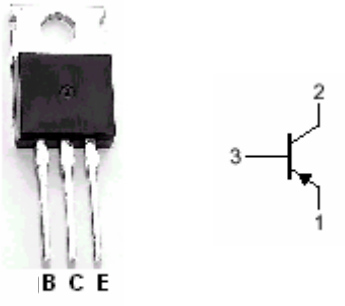

Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA770	Open emitter	-60	V
		2SA771		-80	
V_{CEO}	Collector-emitter voltage	2SA770	Open base	-60	V
		2SA771		-80	
V_{EBO}	Emitter-base voltage		Open collector	-6	V
I_C	Collector current			-6	A
I_B	Base current			-3	A
P_C	Collector power dissipation		T_C=25℃	40	W
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SA770	I_C=-25mA ,I_B=0	-60			V
		2SA771		-80			
V_{CEsat}	Collector-emitter saturation voltage		I_C=-3A; I_B=-0.3A			-1.0	V
I_{CBO}	Collector cut-off current	2SA770	V_{CB}=-60V; I_E=0			-1.0	mA
		2SA771	V_{CB}=-80V; I_E=0				
I_{EBO}	Emitter cut-off current		V_{EB}=-6V; I_C=0			-1.0	mA
h_{FE}	DC current gain		I_C=-1A ; V_{CE}=-4V	40			
f_T	Transition frequency		I_C=-0.5A ; V_{CE}=-12V		10		MHz

Switching times

t_r	Rise time	I_C=-3A ; V_{CC}=-9V I_{B1}=-I_{B2}=-0.4A;R_L=3Ω		0.9		μs
t_{stg}	Storage time			1.0		μs
t_f	Fall time			0.1		μs

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PACKAGE OUTLINE

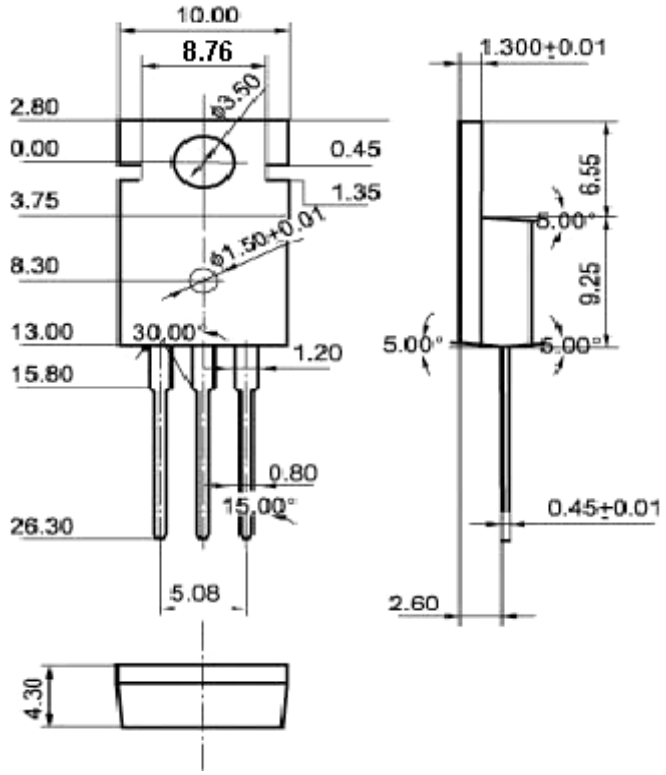

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)